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INFORMATION DISCLOSURE STATEMENT BY APPLICANT							Application Number			
							Filing Date			
							First Named Inventor		Songlin Xu	
							Art Unit		To be assigned	
(use as many sheets as necessary)						Ex		niner Name	To be assigned	
Sheet		1	of		2		Attorney Docket Number		007898 ALRT/ETCH	
				ι	J.S. P/	ATENT	DOC	JMENTS		
Examiner nitials	Cite No.	Document Number Number - Kind Code ² (if known)		Publication Date			Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant		
W	+	US-6,379,575 B1		04-30-2002)2 Y		Figures Appear		
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Examiner nitials	Cite No. '	Foreign Patent Document Country Code® - Number® - Kind Code® (if kni			nown)	Publication MM-DD-		Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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Examiner Signature	Date Considered 4/11/05							

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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